Edward Yi Chang

List of Publications by Year
in descending order

Source: https://exaly.com/author-pdf/11940353/publications.pdf

Version: 2024-02-01

122	1,895	304743	315739
papers	citations	22 h-index	38 g-index

123	123	123	2414
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Coherent phonon manipulation in coupled mechanical resonators. Nature Physics, 2013, 9, 480-484.	16.7	274
2	Layered MoS₂ grown on c â€sapphire by pulsed laser deposition. Physica Status Solidi - Rapid Research Letters, 2015, 9, 187-191.	2.4	130
3	Gate Recessed Quasi-Normally OFF Al₂O₃/AlGaN/GaN MIS-HEMT With Low Threshold Voltage Hysteresis Using PEALD AlN Interfacial Passivation Layer. IEEE Electron Device Letters, 2014, 35, 732-734.	3.9	91
4	GaN MIS-HEMTs With Nitrogen Passivation for Power Device Applications. IEEE Electron Device Letters, 2014, 35, 1001-1003.	3.9	70
5	The Roles of Threading Dislocations on Electrical Properties of AlGaN/GaN Heterostructure Grown by MBE. Journal of the Electrochemical Society, 2010, 157, H746.	2.9	62
6	Oxygen Ion Implantation Isolation Planar Process for AlGaN/GaN HEMTs. IEEE Electron Device Letters, 2007, 28, 476-478.	3.9	44
7	Changes of Electrical Characteristics for AlGaN/GaN HEMTs Under Uniaxial Tensile Strain. IEEE Electron Device Letters, 2009, 30, 213-215.	3.9	43
8	Investigation of Impact Ionization in InAs-Channel HEMT for High-Speed and Low-Power Applications. IEEE Electron Device Letters, 2007, 28, 856-858.	3.9	39
9	Electrical Characteristics of n, p-In_{0.53}Ga_{0.47}As MOSCAPs With In Situ PEALD-AlN Interfacial Passivation Layer. IEEE Transactions on Electron Devices, 2014, 61, 2774-2778.	3.0	39
10	High-Performance Normally-OFF GaN MIS-HEMTs Using Hybrid Ferroelectric Charge Trap Gate Stack (FEG-HEMT) for Power Device Applications. IEEE Electron Device Letters, 2018, 39, 991-994.	3.9	35
11	Simulation study on electrical characteristic of AlGaN/GaN high electron mobility transistors with AlN spacer layer. Japanese Journal of Applied Physics, 2014, 53, 04EF08.	1.5	34
12	High performance UV photodetector based on MoS2 layers grown by pulsed laser deposition technique. Journal of Alloys and Compounds, 2020, 835, 155222.	5.5	34
13	Development of GaN HEMTs Fabricated on Silicon, Silicon-on-Insulator, and Engineered Substrates and the Heterogeneous Integration. Micromachines, 2021, 12, 1159.	2.9	34
14	Growth of High-Quality Ge Epitaxial Layers on Si (100). Japanese Journal of Applied Physics, 2003, 42, L517-L519.	1.5	32
15	High quality Ge thin film grown by ultrahigh vacuum chemical vapor deposition on GaAs substrate. Applied Physics Letters, 2011, 98, .	3.3	32
16	Shape Effect of Silicon Nitride Subwavelength Structure on Reflectance for Silicon Solar Cells. IEEE Transactions on Electron Devices, 2010, 57, 2427-2433.	3.0	30
17	Plasma Enhanced Atomic Layer Deposition Passivated HfO₂/AlN/In_{0.53}Ga_{0.47}As MOSCAPs With Sub-Nanometer Equivalent Oxide Thickness and Low Interface Trap Density. IEEE Electron Device Letters, 2015, 36, 1277-1280.	3.9	30
18	Effects of Wet Chemical and Trimethyl Aluminum Treatments on the Interface Properties in Atomic Layer Deposition of Al₂O₃ on InAs. Japanese Journal of Applied Physics, 2010, 49, 111201.	1.5	29

#	Article	IF	Citations
19	Normally-OFF GaN MIS-HEMT With F^{â^'} Doped Gate Insulator Using Standard Ion Implantation. IEEE Journal of the Electron Devices Society, 2018, 6, 893-899.	2.1	29
20	RF and Logic Performance Improvement of $ hbox{In}_{0.7}hbox{Ga}_{0.3}hbox{As}/hbox{InAs}/hbox{In}_{0.7}hbox{Ga}_{0.3}hbox{As}$ Composite-Channel HEMT Using Gate-Sinking Technology. IEEE Electron Device Letters, 2008, 29, 290-293.	3.9	26
21	High-speed GaAs metal gate semiconductor field effect transistor structure grown on a composite Geâ•GexSi1â^'xâ•Si substrate. Journal of Applied Physics, 2007, 101, 084501.	2.5	24
22	A $delta$-Doped InGaP/InGaAs pHEMT With Different Doping Profiles for Device-Linearity Improvement. IEEE Transactions on Electron Devices, 2007, 54, 1617-1625.	3.0	23
23	The Evolution of Manufacturing Technology for GaN Electronic Devices. Micromachines, 2021, 12, 737.	2.9	23
24	Effects of In-Situ Plasma-Enhanced Atomic Layer Deposition Treatment on the Performance of HfO2/In0.53Ga0.47As Metal-Oxide-Semiconductor Field-Effect Transistors. IEEE Electron Device Letters, 2016, , 1-1.	3.9	21
25	High-Performance GaN MOSHEMTs Fabricated With ALD Al₂O₃Dielectric and NBE Gate Recess Technology for High Frequency Power Applications. IEEE Electron Device Letters, 2017, 38, 771-774.	3.9	21
26	A novel AlGaN/GaN multiple aperture vertical high electron mobility transistor with silicon oxide current blocking layer. Vacuum, 2015, 118, 59-63.	3.5	20
27	Evaluation and Reliability Assessment of GaN-on-Si MIS-HEMT for Power Switching Applications. Energies, 2017, 10, 233.	3.1	19
28	In_{0.53}Ga_{0.47}As FinFET and GAA-FET With Remote-Plasma Treatment. IEEE Electron Device Letters, 2018, 39, 339-342.	3.9	19
29	Study of the inversion behaviors of Al2O3/InxGa1â^'xAs metalâ€“oxideâ€“semiconductor capacitors with different In contents. Solid-State Electronics, 2010, 54, 37-41.	1.4	18
30	High-Performance LPCVD-SiN_x/InAlGaN/GaN MIS-HEMTs With 850-V 0.98-$ext{m}{Omega} cdot$ cm² for Power Device Applications. IEEE Journal of the Electron Devices Society, 2018, 6, 1136-1141.	2.1	18
31	Effect of Postdeposition Annealing Temperatures on Electrical Characteristics of Molecular-Beam-Deposited HfO$_{2}$ on n-InAs/InGaAs Metalâ€“Oxideâ€“Semiconductor Capacitors. Applied Physics Express, 2012, 5, 021104.	2.4	17
32	60 GHz Broadband MS-to-CPW Hot-Via Flip Chip Interconnects. IEEE Microwave and Wireless Components Letters, 2007, 17, 784-786.	3.2	16
33	Numerical calculation of the reflectance of sub-wavelength structures on silicon nitride for solar cell application. Computer Physics Communications, 2009, 180, 1721-1729.	7.5	16
34	Band Alignment Parameters of Al₂O₃/InSb Metalâ€“Oxideâ€“Semiconductor Structure and Their Modification with Oxide Deposition Temperatures. Applied Physics Express, 2013, 6, 061202.	2.4	16
35	A versatile low-resistance ohmic contact process with ohmic recess and low-temperature annealing for GaN HEMTs. Semiconductor Science and Technology, 2018, 33, 095019.	2.0	16
36	The effect of AlN buffer growth parameters on the defect structure of GaN grown on sapphire by plasma-assisted molecular beam epitaxy. Journal of Crystal Growth, 2009, 311, 1487-1492.	1.5	15

#	Article	IF	Citations
37	Electrical Characterization and Materials Stability Analysis of ${m La}_{2}{m O}_{3}/{m HfO}_{2}$ Composite Oxides on n-${m In}_{0.53}{m Ga}_{0.47}{m As}$ MOS Capacitors With Different Annealing Temperatures. IEEE Electron Device Letters, 2013, 34, 1229-1231.	3.9	15
38	Dislocation reduction in GaN film using Ga-lean GaN buffer layer and migration enhanced epitaxy. Thin Solid Films, 2011, 519, 6208-6213.	1.8	14
39	Impact of interfacial misfit dislocation growth mode on highly lattice-mismatched InxGa1-xSb epilayer grown on GaAs substrate by metalorganic chemical vapor deposition. Applied Physics Letters, 2016, 109, .	3.3	14
40	Improved linearity and reliability in GaN metalâ€“oxideâ€“semiconductor high-electron-mobility transistors using nanolaminate La₂O₃/SiO₂ gate dielectric. Japanese Journal of Applied Physics, 2016, 55, 04EG04.	1.5	14
41	Effective Passivation With High-Density Positive Fixed Charges for GaN MIS-HEMTs. IEEE Journal of the Electron Devices Society, 2017, 5, 170-174.	2.1	14
42	AlGaN/GaN MIS-HEMTs With High Quality ALD-Al₂O₃ Gate Dielectric Using Water and Remote Oxygen Plasma As Oxidants. IEEE Journal of the Electron Devices Society, 2018, 6, 110-115.	2.1	14
43	Reliability Characterization of Gallium Nitride MIS-HEMT Based Cascode Devices for Power Electronic Applications. Energies, 2020, 13, 2628.	3.1	14
44	Novel Metamorphic HEMTs With Highly Doped InGaAs Source/Drain Regions for High Frequency Applications. IEEE Transactions on Electron Devices, 2010, 57, 2594-2598.	3.0	13
45	Electrical Characteristics of ${m Al}_{2}{m O}_{3}/{m InSb}$ MOSCAPs and the Effect of Postdeposition Annealing Temperatures. IEEE Transactions on Electron Devices, 2013, 60, 1555-1560.	3.0	13
46	Impact of AlN Interfacial Dipole on Effective Work Function of Ni and Band Alignment of Ni/HfO₂/In_{0.53}Ga_{0.47}As Gate-Stack. IEEE Transactions on Electron Devices, 2015, 62, 3987-3991.	3.0	13
47	Optimal design of the multiple-apertures-GaN-based vertical HEMTs with $$hbox {SiO}_{2}$$ SiO 2 current blocking layer. Journal of Computational Electronics, 2016, 15, 154-162.	2.5	12
48	E-Mode GaN MIS-HEMT Using Ferroelectric Charge Trap Gate Stack With Low Dynamic On-Resistance and High V _{th} Stability by Field Plate Engineering. IEEE Electron Device Letters, 2021, 42, 1268-1271.	3.9	12
49	Comprehensive dynamic on-resistance assessments in GaN-on-Si MIS-HEMTs for power switching applications. Semiconductor Science and Technology, 2018, 33, 055012.	2.0	11
50	Minimum Power Input Control for Class-E Amplifier Using Depletion-Mode Gallium Nitride High Electron Mobility Transistor. Energies, 2021, 14, 2302.	3.1	11
51	Derivation of the Resonance Mechanism for Wireless Power Transfer Using Class-E Amplifier. Energies, 2021, 14, 632.	3.1	11
52	Effect of annealing processes on the electrical properties of the atomic layer deposition Al₂O₃/In_{0.53}Ga_{0.47}As metal oxide semiconductor capacitors. Japanese Journal of Applied Physics, 2014, 53, 04EF04.	1.5	10
53	Potential of Enhancement Mode In_{0.65}Ga_{0.35}As/InAs/In_{0.65}Ga_{0.35}As HEMTs for Using in High-Speed and Low-Power Logic Applications. ECS Journal of Solid State Science and Technology, 2015, 4, N157-N159.	1.8	9
54	Improved Linearity in AlGaN/GaN HEMTs for Millimeter-Wave Applications by Using Dual-Gate Fabrication. ECS Journal of Solid State Science and Technology, 2017, 6, S3106-S3109.	1.8	9

#	Article	IF	Citations
55	InAs Channel-Based Quantum Well Transistors for High-Speed and Low-Voltage Digital Applications. Electrochemical and Solid-State Letters, 2008, 11, H193.	2.2	8
56	Design of Flip-Chip Interconnect Using Epoxy-Based Underfill Up to V-Band Frequencies With Excellent Reliability. IEEE Transactions on Microwave Theory and Techniques, 2010, 58, 2244-2250.	4.6	8
57	Design, Fabrication, and Reliability of Low-Cost Flip-Chip-On-Board Package for Commercial Applications up to 50 GHz. IEEE Transactions on Components, Packaging and Manufacturing Technology, 2012, 2, 402-409.	2.5	8
58	Demonstrating 1â€‰nm-oxide-equivalent-thickness HfO2/InSb structure with unpinning Fermi level and low gate leakage current density. Applied Physics Letters, 2013, 103, 142903.	3.3	8
59	Electrical Analysis and PBTI Reliability of In_{0.53}Ga_{0.47}As MOSFETs With AlN Passivation Layer and NH₃Postremote Plasma Treatment. IEEE Transactions on Electron Devices, 2016, 63, 3466-3472.	3.0	8
60	Design and Fabrication of 0/1-Level RF-Via Interconnect for RF-MEMS Packaging Applications. IEEE Transactions on Advanced Packaging, 2010, 33, 30-36.	1.6	7
61	Methods for Extracting Flat Band Voltage in the InGaAs High Mobility Materials. IEEE Electron Device Letters, 2016, 37, 1100-1103.	3.9	7
62	Low resistive InGaN film grown by metalorganic chemical vapor deposition. Vacuum, 2020, 171, 108974.	3.5	7
63	Nitrogen-Passivated (010) In_{0.53}Ga_{0.47}As FinFETs With High Peak g _m and Reduced Leakage Current. IEEE Transactions on Electron Devices, 2022, 69, 495-499.	3.0	7
64	Sub-10 nm Top Width Nanowire InGaAs Gate-All-Around MOSFETs With Improved Subthreshold Characteristics and Device Reliability. IEEE Journal of the Electron Devices Society, 2022, 10, 188-191.	2.1	7
65	Finite element analysis of antireflective silicon nitride sub-wavelength structures for solar cell applications. Thin Solid Films, 2010, 518, 7204-7208.	1.8	6
66	Effect of Nitridation on the Regrowth Interface of AlGaN/GaN Structures Grown by Molecular Beam Epitaxy on GaN Templates. Journal of Electronic Materials, 2012, 41, 2139-2144.	2.2	6
67	Effects of initial GaN growth mode on the material and electrical properties of AlGaN/GaN high-electron-mobility transistors. Applied Physics Express, 2014, 7, 095502.	2.4	6
68	Performance Enhancement of Flip-Chip Packaged AlGaN/GaN HEMTs Using Active-Region Bumps-Induced Piezoelectric Effect. IEEE Electron Device Letters, 2014, 35, 735-737.	3.9	6
69	Effect of high voltage stress on the DC performance of the Al₂O₃/AlN GaN metalâ€“insulatorâ€“semiconductor high-electron mobility transistor for power applications. Applied Physics Express, 2015, 8, 104102.	2.4	6
70	Effective surface treatment for GaN metalâ€“insulatorâ€“semiconductor high-electron-mobility transistors using HF plus N₂ plasma prior to SiN passivation. Japanese Journal of Applied Physics, 2016, 55, 01AD06.	1.5	6
71	Materials growth and band offset determination of Al2O3/In0.15Ga0.85Sb/GaSb/GaAs heterostructure grown by metalorganic chemical vapor deposition. Applied Physics Letters, 2017, 110, .	3.3	6
72	Hybridization sensing by electrical enhancement with nanoparticles in nanogap. Journal of Vacuum Science & Technology B, 2008, 26, 2572-2577.	1.3	5

#	Article	IF	Citations
73	Bias-Dependent Radio Frequency Performance for 40 nm InAs High-Electron-Mobility Transistor with a Cutoff Frequency Higher than 600 GHz. Japanese Journal of Applied Physics, 2012, 51, 110203.	1.5	5
74	The effect of CdS QDs structure on the InGaP/GaAs/Ge triple junction solar cell efficiency. Electronic Materials Letters, 2014, 10, 457-460.	2.2	5
75	Growth of high-quality In_{0.28}Ga_{0.72}Sb/AlSb/GaSb/GaAs heterostructure by metalorganic chemical vapor deposition for single-channel Sb-based complementary metalâ€“oxideâ€“semiconductor applications. Applied Physics Express, 2017, 10, 075505.	2.4	5
76	AlGaN/GaN Enhancement-Mode MOSHEMTs Utilizing Hybrid Gate-Recessed Structure and Ferroelectric Charge Trapping/Storage Stacked LiNbO₃/HfO₂/Al₂O₃ Structure. IEEE Transactions on Electron Devices, 2021, 68, 3768-3774.	3.0	5
77	AlGaAs/InGaAs High Electron Mobility Transistor Grown on Si Substrate with Ge/GexSi1-xMetamorphic Buffer Layers. Japanese Journal of Applied Physics, 2008, 47, 7069-7072.	1.5	4
78	Fabrication of AlGaN/GaN high electron mobility transistors (HEMTs) on silicon substrate with slant field plates using deep-UV lithography featuring 5W/mm power density at X-band. , 2012, , .		4
79	Câ€“V characteristics of epitaxial germanium metalâ€“oxideâ€“semiconductor capacitor on GaAs substrate with ALD Al2O3 dielectric. Microelectronic Engineering, 2012, 97, 16-19.	2.4	4
80	Ge epitaxial films on GaAs (100), (110), and (111) substrates for applications of CMOS heterostructural integrations. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2013, 31, .	1.2	4
81	Investigation of Multilayer TiNi Alloys as the Gate Metal for nMOS In_{0.53}Ga_{0.47}As. IEEE Transactions on Electron Devices, 2016, 63, 4714-4719.	3.0	4
82	InGaAs QW-MOSFET Performance Improvement Using a PEALD-AlN Passivation Layer and an <italic>In-Situ</italic> NH₃Post Remote-Plasma Treatment. IEEE Electron Device Letters, 2017, 38, 310-313.	3.9	4
83	Demonstrating antiphase domain boundary-free GaAs buffer layer on zero off-cut Si (0â€‰0â€‰1) substrate for interfacial misfit dislocation GaSb film by metalorganic chemical vapor deposition. Materials Research Express, 2017, 4, 085901.	1.6	4
84	A New GaN-Based Device, P-Cascode GaN HEMT, and Its Synchronous Buck Converter Circuit Realization. Energies, 2021, 14, 3477.	3.1	4
85	Hf-Based and Zr-Based Charge Trapping Layer Engineering for E-Mode GaN MIS-HEMT Using Ferroelectric Charge Trap Gate Stack. IEEE Journal of the Electron Devices Society, 2022, 10, 525-531.	2.1	4
86	A 60-nm-thick enhancement mode In0.65Ga0.35As/InAs/In0.65Ga0.35As high-electron-mobility transistor fabricated using Au/Pt/Ti non-annealed ohmic technology for low-power logic applications. Applied Physics Express, 2016, 9, 026502.	2.4	3
87	Study of the interface stability of the metal (Mo, Ni, Pd)/HfO2/AlN/InGaAs MOS devices. AIP Advances, 2017, 7, 085208.	1.3	3
88	Nonlinear dependence of X-ray diffraction peak broadening in InxGa1â^'xSb epitaxial layers on GaAs substrates. Applied Physics Express, 2018, 11, 045503.	2.4	3
89	Analysis of Instability Behavior and Mechanism of E-Mode GaN Power HEMT with p-GaN Gate under Off-State Gate Bias Stress. Energies, 2021, 14, 2170.	3.1	3
90	Investigation of Multiple-Mesa-Nanochannel Array GaN-Based MOSHEMTs with Al2O3 Gate Dielectric Layer. ECS Journal of Solid State Science and Technology, 2021, 10, 055017.	1.8	3

#	Article	IF	Citations
91	Electrical Characterization and Transmission Electron Microscopy Assessment of Isolation of AlGaN/GaN High Electron Mobility Transistors with Oxygen Ion Implantation. Japanese Journal of Applied Physics, 2010, 49, 021001.	1.5	2
92	Room temperature self-organized gold nanoparticles materials for embedded electronic devices. Journal of Materials Science: Materials in Electronics, 2013, 24, 376-381.	2.2	2
93	Investigation of Characteristics of Al2O3/n-In x Ga1â^'x As (xÂ=Â0.53, 0.7, and 1) Metalâ€“Oxideâ€“Semiconductor Structures. Journal of Electronic Materials, 2013, 42, 2439-2444.	2.2	2
94	Performance Evaluation of InGaSb/AlSb P-Channel High-Hole-Mobility Transistor Faricated Using BCl3Dry Etching. Japanese Journal of Applied Physics, 2013, 52, 020203.	1.5	2
95	Performance Enhancement of Flip-Chip Packaged AlGaN/GaN HEMTs by Strain Engineering Design. IEEE Transactions on Electron Devices, 2016, 63, 3876-3881.	3.0	2
96	Entirely relaxed lattice-mismatched GaSb/GaAs/Si(001) heterostructure grown via metalorganic chemical vapor deposition. Applied Physics Express, 2018, 11, 051202.	2.4	2
97	Communicationâ€"Potential of the Ï€-Gate InAs HEMTs for High-Speed and Low-Power Logic Applications. ECS Journal of Solid State Science and Technology, 2019, 8, P319-P321.	1.8	2
98	The effect of a Sb and Ga intermediate layer on the interfacial layer properties of epitaxial GaSb on GaAs grown by metalorganic chemical vapor deposition. Thin Solid Films, 2019, 669, 430-435.	1.8	2
99	Enhancement of electron transport properties of InAlGaN/AlN/GaN HEMTs on silicon substrate with GaN insertion layer. Applied Physics Express, 2020, 13, 065501.	2.4	2
100	Control of V _{th} of the enhancement high-frequency AlGaN/GaN HEMT fabricated by oxygen-based digital etching. Applied Physics Express, 2021, 14, 126501.	2.4	2
101	Evaluation of RF and Logic Performance for 80 nm InAs/InGaAs Composite Channel HEMTs Using Gate Sinking Technology. , 2007, , .		1
102	InAs-Channel Metal-Oxide-Semiconductor HEMTs with Atomic-Layer-Deposited Al[sub 2]O[sub 3] Gate Dielectric. Electrochemical and Solid-State Letters, 2009, 12, H456.	2.2	1
103	InAs-Channel High-Electron-Mobility Transistors for Ultralow-Power Low Noise Amplifier Applications. Japanese Journal of Applied Physics, 2009, 48, 04C094.	1.5	1
104	Experimental and Modeling on Atomic Layer Deposition Al2O3/n-InAs Metal-Oxide-Semiconductor Capacitors with Various Surface Treatments. ECS Transactions, 2011, 34, 1041-1046.	0.5	1
105	Influence of post deposition annealing temperatures on electrical properties of Al<inf>2</inf>O<inf>3</inf>/InSb MOSCAPs. , 2012, , .		1
106	An Au-free GaN high electron mobility transistor with Ti/Al/W Ohmic metal structure. , 2015, , .		1
107	Enhancement-mode AlGaN/GaN MIS-HEMTs with low threshold voltage hysteresis using damage-free neutral beam etched gate recess. , 2016, , .		1
108	Electrical Properties of Compound 2D Semiconductor Mo<inf>1â^'x</inf>Nb<inf>x</inf>S<inf>2</inf>. , 2018, , .		1

#	Article	IF	Citations
109	Analysis of High-Frequency Behavior of AlGaN/GaN HEMTs and MIS-HEMTs under UV Illumination. ECS Journal of Solid State Science and Technology, 2021, 10, 055004.	1.8	1
110	Dependence of GaN Defect Structure on the Growth Temperature of the AlN Buffer Layer. Materials Research Society Symposia Proceedings, 2008, 1068, 1.	0.1	0
111	On the noise performance of 80nm InAs/In<inf>0.7</inf>Ga<inf>0.3</inf>As HEMTs using gate sinking technology. , 2008, , .		0
112	An AlGaAs/InGaAs HEMT Grown on Si Substrate with Ge/GexSi1-x Metamorphic Buffer Layers. Materials Research Society Symposia Proceedings, 2008, 1068, 1.	0.1	0
113	A 40-nm-Gate InAs/In<inf>0.7</inf>Ga<inf>0.3</inf>As Composite-Channel HEMT with 2200 mS/mm and 500-GHz f<inf>T</inf>. , 2009, , .		0
114	An Al[sub 2]O[sub 3] AlGaAs/InGaAs Metal-Oxide-Semiconductor PHEMT SPDT Switch with Low Control Currents for Wireless Communication Applications. Electrochemical and Solid-State Letters, 2010, 13, H219.	2.2	0
115	3D finite element simulation of morphological effect on reflectance of Si<inf>3</inf>N<inf>4</inf> sub-wavelength structures for silicon solar cells. , 2011, , .		0
116	Impact of bonding temperature on the performance of In<inf>0.6</inf>Ga<inf>0.4</inf>As Metamorphic High Electron Mobility Transistor (mHEMT) device packaged using Flip-Chip-on-Board (FCOB) technology. , 2012, , .		0
117	Studying of InSb MOS capacitors for post CMOS application. , 2013, , .		0
118	High quality Ge epitaxial films grown on In<inf>0.51</inf>Ga<inf>0.49</inf>P/GaAs and GaAs substrates by ultra high vacuum chemical deposition. , 2014, , .		0
119	The effect of surface passivation on the electrical performance of Al-GaN/GaN HEMTs with slant field plates. , 2016, , .		0
120	Study on the electrical characteristics of in situ PEALD-passivated HfO2/In0.53Ga0.47As MOSCAP and MOSFET structures. , 2016, , .		0
121	Evaluation of AlGaN/GaN metalâ€“oxideâ€“semicondutor high-electron mobility transistors with plasma-enhanced atomic layer deposition HfO‹sub›2‹/sub›/AlN date dielectric for RF power applications. Japanese Journal of Applied Physics, 2017, 56, 094101.	1.5	0
122	Extraction of Bias-dependent Source and Drain Resistances in AlGaN/GaN MIS-HEMTs Using Pulsed Measurement Method. ECS Journal of Solid State Science and Technology, 2022, 11, 065008.	1.8	0